	L #	Hits	Search Text	DBs	Time Stamp
1	L1	149121		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
2	L2	4285	(427/569-579,562-564,530).C	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:03
3	L3	1346	(118/723E-723IR).CCLS.	USPAT;- US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:04
4	L4	275		USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:04
5	L5	184222	boron boride "BCl.sub.3" "BF.sub.3" "BX.sub.3"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:06

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		L	#	Hits	Search Text	DBs	Time Stamp
	6	L6		65	4 and 5	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:06
	7	L7		157409 8	pulse near 3 duration period pause	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:08
	8	L8	= = =	54	6 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:08
	9	L9		11	6 not 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/17 16:08
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		Document ID	Issue Date	Title	Current OR	Inventor
30%	1 -	US 200100412 30 A1 37/] Bunday 1-	20011115 → 1/23/97	producing wear-resi stant boride		Hunger, Hans-Jorg et al.
	2	US 6342277 B1	20020129	Sequentia l chemical vapor depositio n	427/562	Sherman, Arthur
2]	3	US 6335536 B1	20020101 14/99	Method and apparatus for low voltage plasma doping using dual pulses	250/492.3	Goeckner, Matthew J. et al.
	4	US 6306225 B1	20011023	Process for producing wear-resi stant boride layers on metallic material surfaces	148/241	Hunger, Hans-Jorg et al.
	5	US 6281147 B1	20010828	Plasma CVD method	438/788	Yamazaki, Shunpei et al.

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		Document ID	Issue Date	Title	Current OR	Inventor
	6	US 6200651 B1	20010313	Method of chemical vapor depositio n in a vacuum plasma processor responsive to a pulsed microwave source	427/571	Roche, Gregory A. et al.
#2	7	US 6182604 B1	20010206 N/29	Hollow cathode for plasma doping system	118/723E	Goeckner, Matthew J. et al.
	8	US 6162709 A	20001219	Use-of an asymmetri c waveform to control ion bombardme nt during substrate processin g	438/513	Raoux, Sebastien et al.
Abs-	101 pu 126 9	lan pused DC D3 courts took US 6139921 A(4-65-0	Method for depositin g fine-grai ned alumina coatings on cutting tools	427/576	Taschner, Christine et al.
	10	US 6136388 A	20001024	Substrate processin g chamber with tunable impedance	427/569	Raoux, Sebastien et al.

		Document ID	Issue Date	Title	Current OR	Inventor	•
#4	11	powder ce pulous plu US 6124564 A pow date	20000926 1 /23/18	Hardfacin g compositi ons and hardfacin g coatings formed by pulsed plasma-tr ansferred arc	219/121.4 7	Sue, J. Albert et al.	
50-50 #5	12 The pu	plasma CV palacolnam necovare US 6110542 A 413 SPAJINIX uni 1-30ms	20000829 of Fd 92341	Method for forming a film	427/577	Miyanaga, Akiharu et al.	
	13	US 6101971 A	20000815	Ion implantat ion control using charge collectio n, optical emission spectrosc opy and mass analysis		BN fm dub Denholm, A. Stuart et al.	eron "Ne
	14	US 6098568 A	20000808	Mixed	118/723E	Raoux, Sebastien et al.	
(Ab) Control 10N/10	dios A	us 6096160 A	plasma 20000801 elt.fd.aps	Helicon wave plasma processin g apparatus	156/345	Kadomura, Shingo	
	The on this waste	est sig. feets	palarpurel = 1 BC/3 flow	signed of Ils copsec & pur	en Sporod Le widhigge Clasto; N	opse 2=10	

	Document ID	Issue Date	Title	Current OR	Inventor
16	US 6055928 A	20000502	Plasma immersion ion processor for fabricati ng semicondu ctor integrate d circuits	118/723E	Murzin, Ivan Herman et al.
17	US 6041734 A	20000328	Use of an asymmetri c waveform to control ion bombardme nt during substrate processin g	118/723E	Raoux, Sebastien et al.
18	US 6015762 A	20000118	Plasma CVD method	438/788	Yamazaki, Shunpei et al.
19	US 5988103 A	19991123	Apparatus for plasma source ion implantat ion and depositio n for cylindric al surfaces	118/723E	Fethersto n, Robert P. et al.

		Document	Issue	Title	Current OR	Inventor
(D)F	20	ID Lows Lows Logola US 5983828 A	19991116)	processin g of a semicondu ctor substrate	118/723I	Savas, Stephen E.
good for #8	3evan 21 Adiso	metron in back US 5981078 A Mp. J. PCVI) in 2001, pube	9000 Clost 19991109 201 Public 2/24 DE public Unda 20186	Composite body and Coprocess for its production	Cavhu-n Hotoolo 428/457	Tabersky, Ralf et
	22	US	19990810	Pulsed high energy	219/121.5 9	Witherspo on, F. Douglas et al.
oppaly #9	23	ouls. I have villed synchronized US 5928528 A	19990727 9/2/97	treatment method and plasma treatment		Kubota, Masafumi et al.
	24	US 5900289 A		Method of producing a coloratin g coating		Hartmann, Rolf et al.
	25	US 5897713 A	19990427	Plasma generatin g apparatus	118/723I	Tomioka, Kazuhiro et al.

		Document ID	Issue Date	Title	Current OR	Inventor
off #10	(Ab) 26	pulsent plu- predetime of a pulsed US 5883016 A	up, heze	Apparatus and method for hydrogena fing polysilic on thin film transisto rs by plasma immersion implantat	438/798	Chan, Chung et al.
114		F13.6-good But physical US 5837331 A ento figl. ed.	vassing app.	ion Amorphous multi-lay ered structure and method of making the same	t. · → ·	Menu, Eric P. et al.
`\ .	28	US 5693376 A	19971202	Method for plasma source ion implantat ion and depositio n for cylindric al surfaces	427/523	Fethersto n, Robert P. et al.

		Document ID	Issue Date	Title	Current OR	Inventor
#12	29 Fo D) A	US 15654043 A 5,5 B druss sufund mode pulsed drush	19970805 for BF3 later circust to	Pulsed plate plasma implantat ion system and method	427/527	Shao, Jiqun et al.
	30	IIC		Method and apparatus for a large volume	118/723MP	Eastlund, Bernard J.
#5=#13	#12 111 31	US 5626922 A	19970506	Plasma processin g method		Miyanaga, Akiharu et al.

		Document ID	Issue Date	Title	Current OR	Inventor
AH.	32	us 5607264 A	19970304	Tool with diamond cutting edge having vapor deposited metal oxide layer and a method of making and using such tool	407/118	Konig, Udo et al.
Apparat HB	(Ab) Box 33 Bhe	Susma achul dus in Budug US- 5587233 A Senorl duch	ond. Wpulsed ron-lusts 19961224 . 20µs-20ms	Direct volts, Composite body and its use	428/325	Konig, Udo-et al.
*16	34	US 5587207 A	19961224	Arc assisted CVD coating and sintering method	427/571	Gorokhovs ky, Vladimir I.
	35	US 5558718 A	19960924	Pulsed source ion implantat ion apparatus and method		Leung, Ka-Ngo

		Document ID	Issue Date	Title	Current OR	Inventor	!/
#17		US 5547716 A	19960820	Laser absorptio n wave depositio n process and apparatus		Thaler, Stephen L.	
	(A)) dame	-dust-	apparatus 10 5 Pulse d	duct vil.		
也18	37	US 5516588 A	19960514	Composite body, its use and a process for its production	120/160	van den Berg, Hendrikus et al.	the the (M)
e meghebil er hebbe	· = ·	but see cla	¥				
#M	At)cBN		Tool with wear-resi stant cutting edge made of cubic boron nitride or polycryst alline cubic boron nitride, a method of manufactu ring the tool and its use	428/216	Konig, Udo et al.	
	39	US 5397428 A	19950314	Nucleatio n enhanceme nt for chemical vapor depositio n of diamond	117/86	Stoner, Brian R. et al.	

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		Document ID	Issue Date	Title	Current OR	Inventor	
4W	40 (D)	ID (Time β US 5354381 A promotel PT 9F2	F3 ploon- 19941011 3 pulsa-ull	Plasma immersion ion implantat ion '(PI.sup.3) apparatus	118/723E	Sheng, Terry T.	
#21	l	Julou H US 5304407 A		Method	427/569	Hayashi, Shigenori et al.	
*22	4.2	US '\$289010 A) 19940222	Ion purificat ion for plasma ion implantat ion	250/492.2 1	Shohet, Juda L.	
AV)	43	US 5192578 A	19930309	Method of producing coating using negative DC pulses with specified duty factor	427/576	Ramm, Jurgen et al.	
#24	44	US 5173328 A		Plasma CVD process for coating a basic metallic body with a non-condu ctive coating material	•	Reiter, Norbert et al.	white way

		Document ID	Issue Date	Title	Current OF	Inventor
	45	US 5130170 A	19920714	Microwave PCVD method for continuou sly forming a large area functiona l deposited film using a curved moving substrate web with microwave energy with a directivi ty in one direction perpendic ular to the direction of microwave propagati on	427/575	Kanai, Masahiro et al.
/	400	US 5098483 A	19920324	Methods of treating spherical surfaces	423/497	Little, Roger G. et al.
1	47 (p)J	US 5078848 A rstrol & Uva nstrol & Uva pro Rx =	19920107 BN	Procedure and apparatus for the coating of materials by means of a pulsating plasma	: / / / / /	Anttila, Asko et al.

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		IIIG		Title	Current OR	Inventor
	48			Plasma doping process and apparatus therefor	438/513	Nakayama, Ichiro et al.
	49	US 4937094 A `	19900626	Method of creating a high flux of activated species for reaction with a remotely located substrate	427/574	Doehler, Joachim et al.
	50	US 4883686 A	19891128	Methodfor the high rate plasma deposition of high quality material	•	Doehler, Joachim et al.
1	51	US 4764394 A	19880816	Method and apparatus for plasma source ion implantat ion	427/525	Conrad, John R.
	52	US 4762756 A	19880809	Thermoche mical surface treatment s of materials in a reactive gas plasma		Bergmann, Erich et al.

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		Document ID	Issue Date	Title	Current OR	Inventor
\$100	53	US 4645895 A	19870224	Method and apparatus for surface-t reating workpiece s	219/76.13	Boxman, Raymond L. et al.
	54	US 4568563 A	10060204	Optical fibre manufactu re		Jackson, Thomas M. et al.